

Applications

- IEEE802.11b DSSS WLAN
- IEEE802.11g,n OFDM WLAN
- Embedded applications

Features

- ❑ Integrates SP3T Switch and LNA with by-pass mode
- ❑ 12 dB gain,
- ❑ 1.8 dB NF
- ❑ 0.5 dB Bluetooth path loss
- ❑ 1.07x1.05x 0.38mm, 250 um pitch, SnAg solder bump
- ❑ Lead free, Halogen free and RoHS compliant

Product Description

The SE2600S is a single chip integrated front-end module (FEM) with a Bluetooth port to complement WLAN chipsets with integrated Power Amplifier. The FEM integrates SP3T Switch and Low Noise Amplifier with bypass mode in an ultra compact package. It is capable of switching between WLAN RX, WLAN TX and Bluetooth™

Ordering Information

Part No.	Package	Remark
SE2600S	11 pin CSP	Samples
SE2600S-R	11 pin CSP	Tape and Reel
SE2600S-EK1	N/A	Evaluation kit

Functional Block Diagram

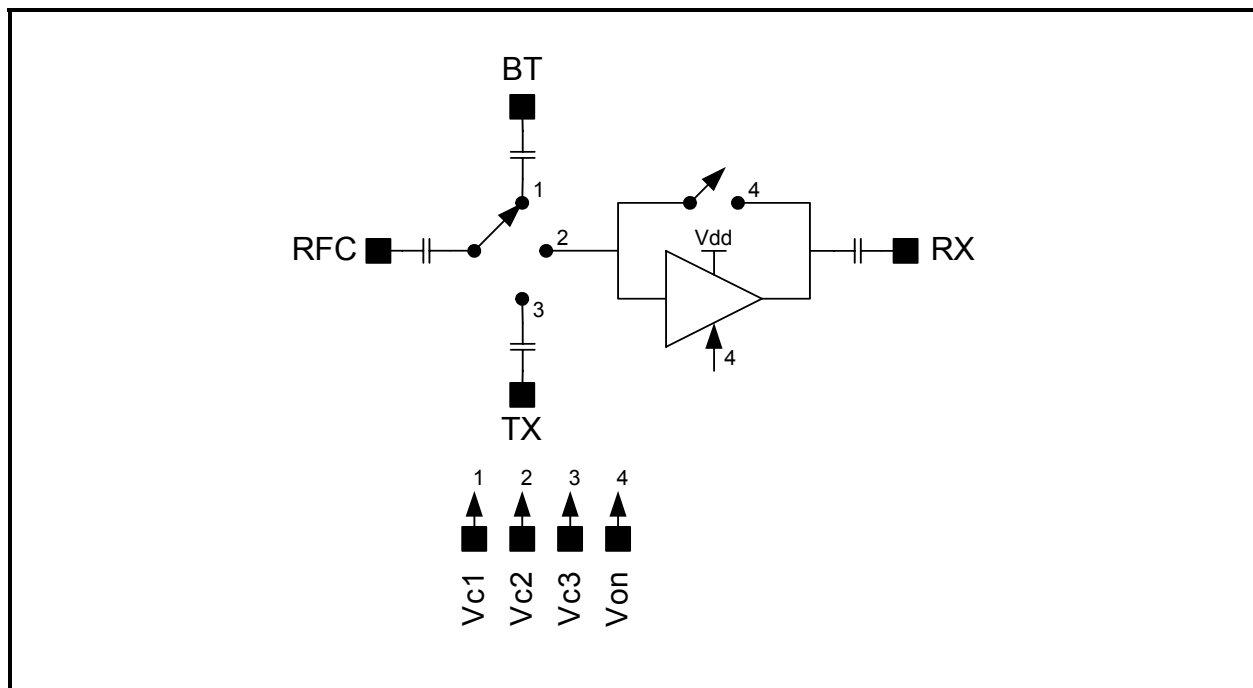


Figure 1: Functional Block Diagram

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Product Preview

The datasheet contains information from the product concept specification. SiGe Semiconductor, Inc. reserves the right to change information at any time without notification.

Preliminary Information

The datasheet contains information from the design target specification. SiGe Semiconductor, Inc. reserves the right to change information at any time without notification.

Production testing may not include testing of all parameters.

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